GSMDEC2210V

20V Dual N-Channel MOSFETs

Product Description

These Dual N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

Features

- 20V, 30A, $R_{DS(ON)}$=12mΩ@V_{GS}=10V
- Improved dv/dt capability
- ESD Protection Diode Embedded
- 100% EAS guaranteed
- Green Device Available
- DFN3X3-8L package design

Applications

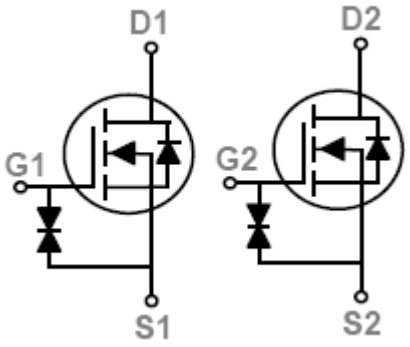
- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR
- Li-Battery Protection

Packages & Pin Assignments

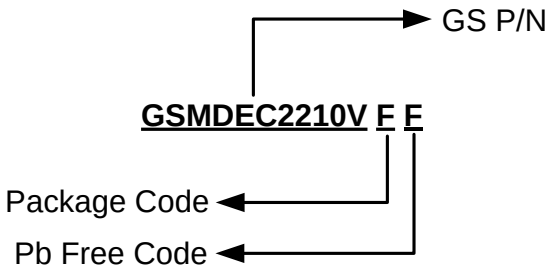
GSMDEC2210VFF (DFN3X3-8L)

Top View

Pin	Description
1	Source 1
2	Gate 1
3	Source 2
4	Gate 2
5	Drain 2
6	Drain 2
7	Drain 1
8	Drain 1

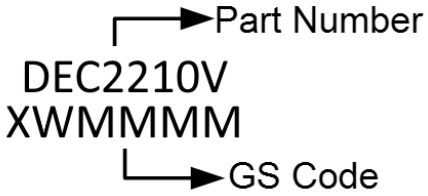


Ordering Information



Part Number	Package	Quantity
GSMDEC2210VFF	DFN3X3-8L	3000 pcs

Marking Information



Absolute Maximum Ratings

T_A=25ºC Unless otherwise noted

Symbol	Parameter		Typical	Unit
V_{DS}	Drain-Source Voltage		20	V
V_{GS}	Gate-Source Voltage		±10	V
I_D	Continuous Drain Current	T_A=25℃	30	A
		T_A=100℃	19	
I_{DM}	Pulsed Drain Current		120	A
P_D	Power Dissipation (T_A=25℃)		26	W
	Power Dissipation (Derate above 25℃)		0.21	W/℃
T_J	Operating Junction Temperature Range		-55 to +150	℃
T_{STG}	Storage Temperature Range		-55 to +150	℃
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		62	℃/W
$R_{\theta JC}$	Thermal Resistance-Junction to Case		4.8	℃/W

Note 1: Repetitive Rating : Pulsed width limited by maximum junction temperature.

Electrical Characteristics

T_A=25℃ Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	20			V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃, I_D=1mA		0.02		V/℃
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	0.3	0.6	1	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient			2		mV/℃
I_{GSS}	Gate Leakage Current	V_{DS}=0V, V_{GS}=±10V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V			1	uA
		V_{DS}=16V, V_{GS}=0V, T_J=125℃			10	
I_S	Continuous Source Current	V_G=V_D=0V, Force Current			30	A
I_{SM}	Pulsed Source Current				60	
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=4.5V, I_D=5A		10	12	mΩ
		V_{GS}=2.5V, I_D=3A		11	14	
		V_{GS}=1.8V, I_D=2A		13	20	
g_{FS}	Forward Transconductance	V_{DS}=10V, I_S=5A		12		S
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_S=1A			1	V
Dynamic						
Q_g	Total Gate Charge	V_{DS}=10V, V_{GS}=4.5V, I_D=5A		16.9	26	nC
Q_{gs}	Gate-Source Charge			1.1	3	
Q_{gd}	Gate-Drain Charge			4	7	
C_{iss}	Input Capacitance	V_{DS}=10V,V_{GS}=0V, f=1MHz		1020	1480	pF
C_{oss}	Output Capacitance			160	240	
C_{rss}	Reverse Transfer Capacitance			110	160	
$t_{d(on)}$	Turn-On Time	V_{DD}=10V, I_D=1A, V_{GS}=4.5V, R_G=25Ω		6.8	13	ns
t_r				20	38	
$t_{d(off)}$	Turn-Off Time			41.8	79	
t_f				13.2	25	

Note 2: The data tested by pulsed , pulse width≦300us, duty cycle≦2%.

Note 3: Essentially independent of operating temperature.

Typical Performance Characteristics

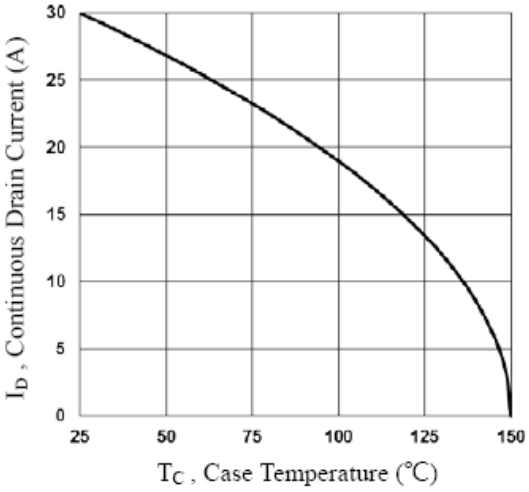


Fig.1 Continuous Drain Current vs. T_c

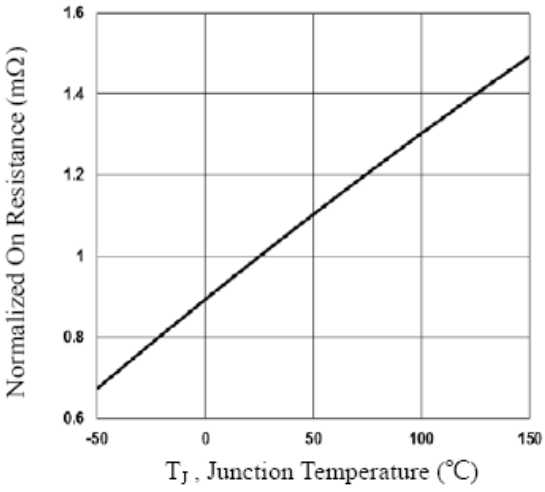


Fig.2 Normalized RDSON vs. T_J

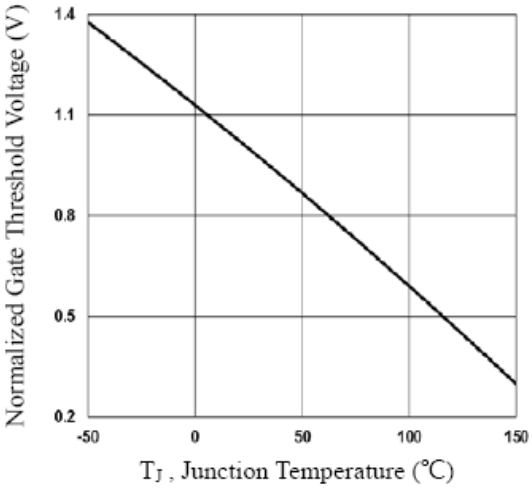


Fig.3 Normalized V_{th} vs. T_J

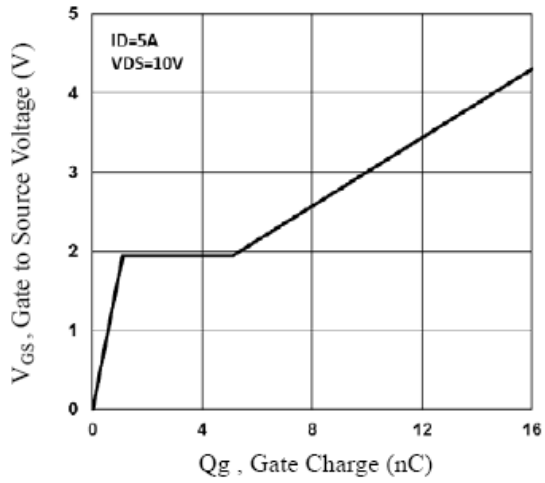


Fig.4 Gate Charge Waveform

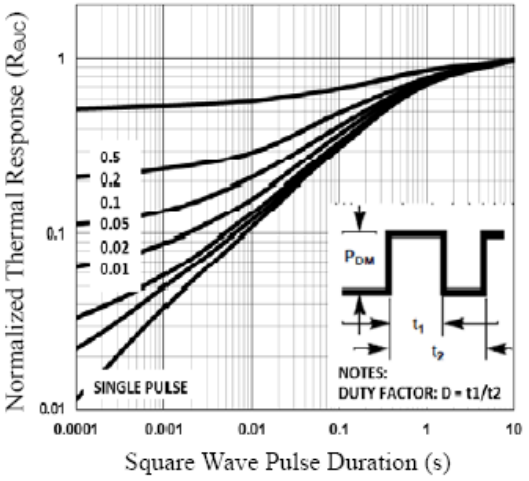


Fig.5 Normalized Transient Response

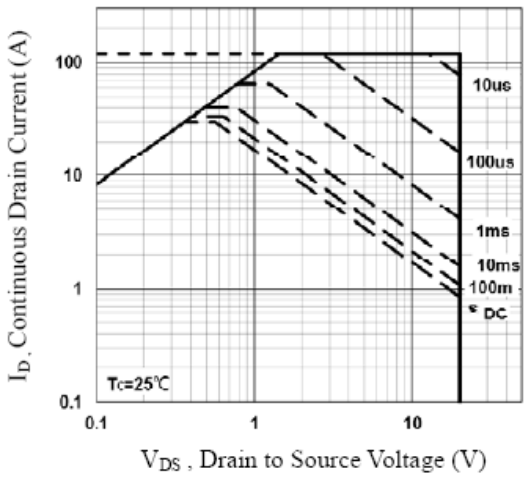
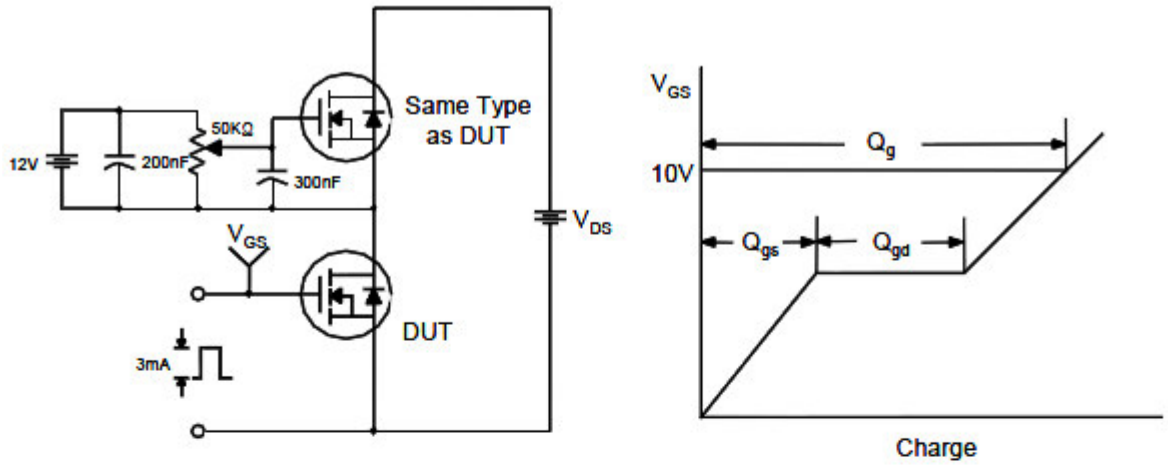


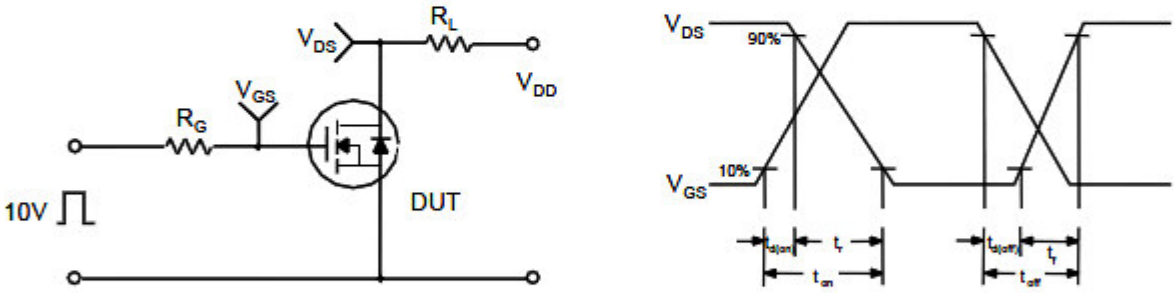
Fig.6 Maximum Safe Operation Area

Typical Performance Characteristics (Continue)

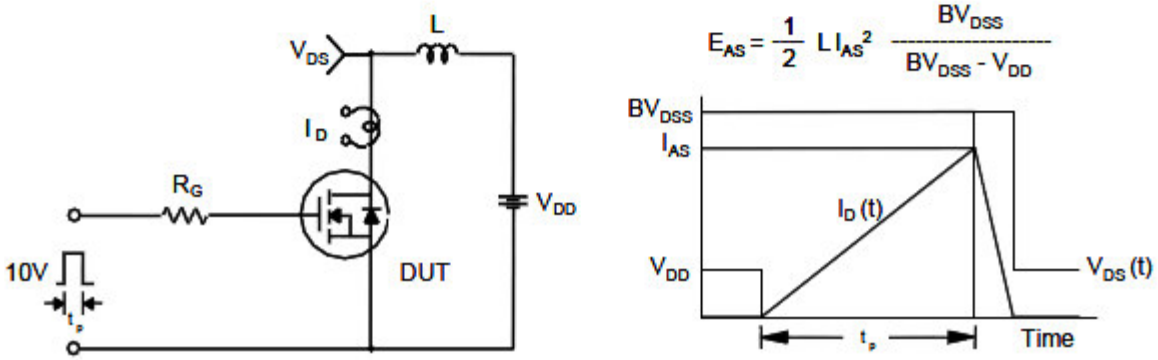
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

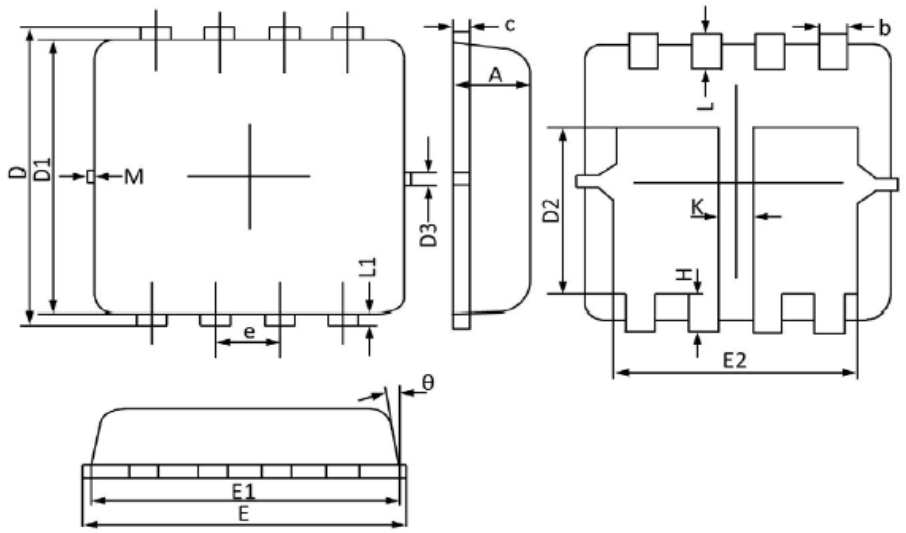


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

DFN3X3-8L



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
b	0.250	0.350	0.010	0.013
c	0.100	0.250	0.004	0.009
D	3.250	3.450	0.128	0.135
D1	3.000	3.200	0.119	0.125
D2	1.780	1.980	0.070	0.077
D3	0.130 (REF)		0.005 (REF)	
E	3.200	3.400	0.126	0.133
E1	3.000	3.200	0.119	0.125
E2	2.390	2.590	0.094	0.102
e	0.650 (BSC)		0.026 (BSC)	
H	0.300	0.500	0.011	0.019
L	0.300	0.500	0.011	0.019
L1	0.130 (REF)		0.005 (REF)	
K	0.300 (REF)		0.012 (REF)	
θ	0°	12°	0°	12°
M	0.150 (REF)		0.006 (REF)	

NOTICE

Information furnished is believed to be accurate and reliable. However Globaltech Semiconductor assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties, which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Globaltech Semiconductor. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information without express written approval of Globaltech Semiconductor.

CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587